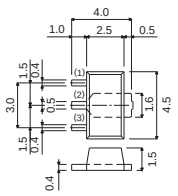
High gain amplifier transistor (25V, 2A)

2SD2153

●Features

1) Low saturation voltage,
   typically $V_{CE(sat)}$ = 0.12V at I_C = I_B = 1A / 20mA
2) Excellent DC current gain characteristics.

●Dimensions (Unit : mm)



(1) Base
(2) Collector
(3) Emitter

ROHM : MPT3
EIAJ : SC-62

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	2	A(DC)
		3	A(Pulse) *1
Collector power dissipation	P_C	0.5	W
		2 *2	
Junction temperature	Tj	150	°C
Storage temperature	Tstg	−55 to +150	°C

*1 Single pulse, Pw=10ms
*2 Mounted on a 40×40×0.7mm Ceramic substrate

●Packaging specifications and h_{FE}

Type	2SD2153
Package	MPT3
h_{FE}	UVW
Marking	DN *
Code	T100
Basic ordering unit (pieces)	1000

* Denotes h_{FE}

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	30	–	–	V	I_C=50μA
Collector-emitter breakdown voltage	BV_{CEO}	25	–	–	V	I_C=1mA
Emitter-base breakdown voltage	BV_{EBO}	6	–	–	V	I_E=50μA
Collector cutoff current	I_{CBO}	–	–	0.5	μA	V_{CB}=20V
Emitter cutoff current	I_{EBO}	–	–	0.5	μA	V_{EB}=5V
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	0.12	0.5	V	I_C/I_B=1A/20mA *
DC current transfer ratio	h_{FE}	820	–	1800	–	V_{CE}/I_C=6V/0.5A
Transition frequency	f_T	–	110	–	MHz	V_{CE}=10V, I_E=−10mA , f= 100MHz
Output capacitance	Cob	–	22	–	pF	V_{CB}=10V, I_E=0A , f =1MHz

* Measured using pulse current.

●Electrical characteristics curves

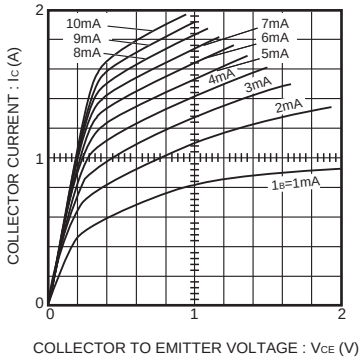


Fig.1 Ground emitter output characteristics

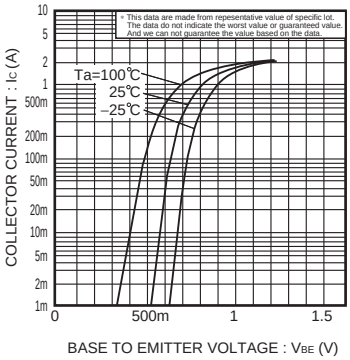


Fig.2 Ground emitter propagation characteristics

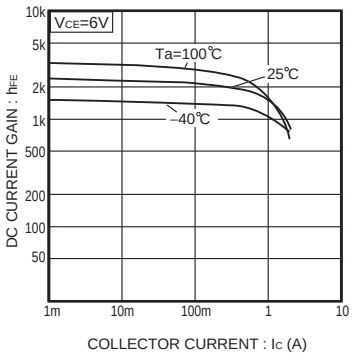


Fig.3 DC current gain

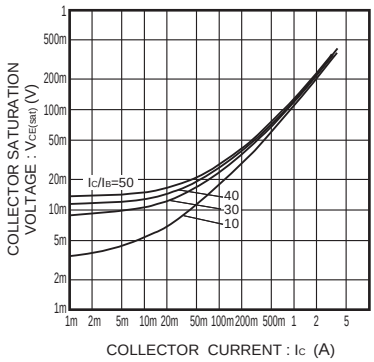


Fig.4 Collector-emitter saturation voltage vs. collector current

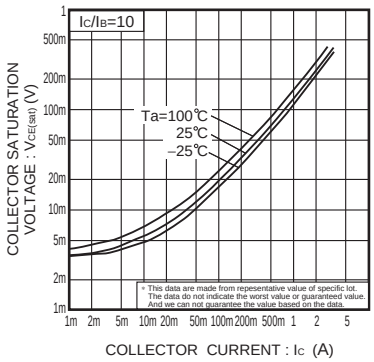


Fig.5 Collector-emitter saturation voltage vs. collector current

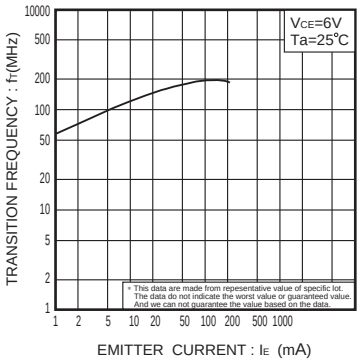


Fig.6 Gain bandwith product vs. emitter current

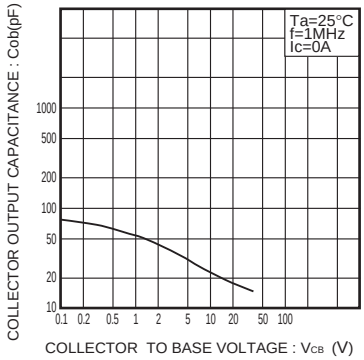


Fig.7 Collector output capacitance vs. collector-base voltage

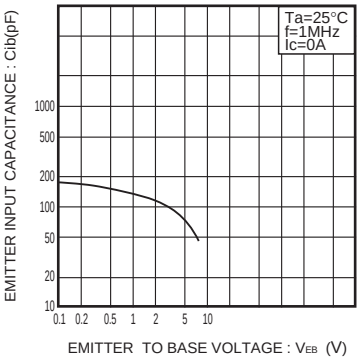


Fig.8 Emitter input capacitance vs. emitter-base voltage

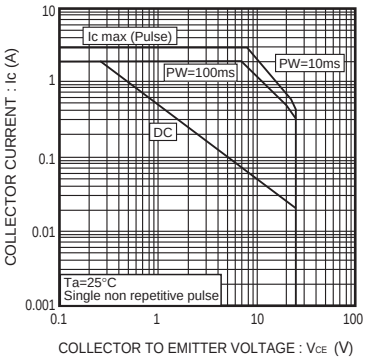


Fig.9 Safe operating area

Notes

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